

**isc Silicon NPN Power Transistor**

**2SD2061**

**DESCRIPTION**

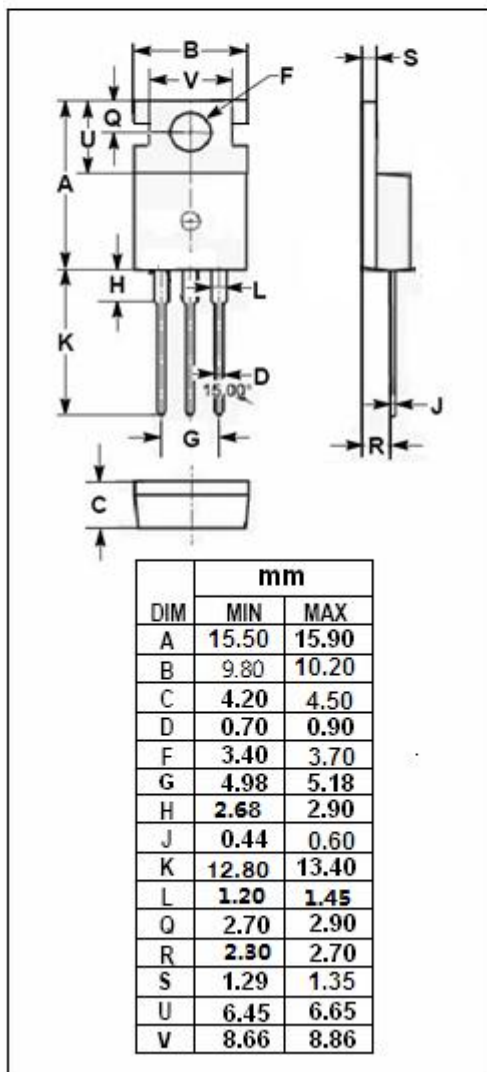
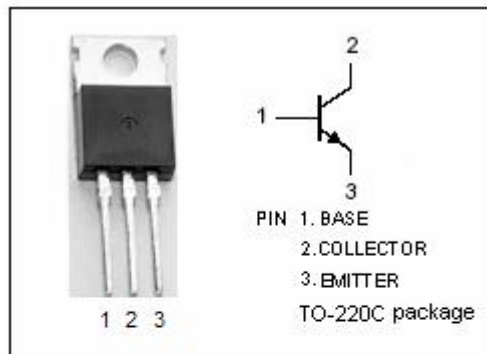
- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = 0.3V(TYP.) @ I_C = 2A$
- Collector Power Dissipation  
:  $P_C = 30W (Max)$
- Wide Area of Safe Operation

**APPLICATIONS**

- Designed for low frequency power amplifier applications

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	80	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	3	A
$I_{CM}$	Collector Current-Pulse	6	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ C$	30	W
	Collector Power Dissipation @ $T_a = 25^\circ C$	2.0	
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



**isc Silicon NPN Power Transistor****2SD2061****ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA ; I <sub>B</sub> = 0	60			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 50 μ A ; I <sub>E</sub> = 0	80			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 50 μ A ; I <sub>C</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.2A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.2A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 60V; I <sub>E</sub> = 0			10	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> =0			10	μ A
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 5V	100		320	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 5V		8		MHz
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1.0MHz		70		pF